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- EPIC™ (Enhanced-Performance Implanted CMOS) 2-µ Process
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 > 2 V at V_{CC}, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) 300-mil DIPs

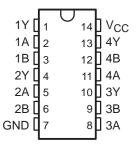
description

These quadruple 2-input positive-NOR gates are designed for 2.7-V to 5.5-V V_{CC} operation.

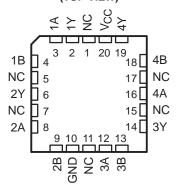
The 'LV02 perform Boolean function $Y = \overline{A + B}$ or $Y = \overline{A} \bullet \overline{B}$ in positive logic.

The SN74LV02 is available in Tl's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

SN54LV02...J OR W PACKAGE SN74LV02...D, DB, OR PW PACKAGE (TOP VIEW)



SN54LV02...FK PACKAGE (TOP VIEW)



NC - No internal connection

The SN54LV02 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV02 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE (each gate)

INP	UTS	OUTPUT
Α	В	Υ
Н	Х	L
Х	Н	L
L	L	Н



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

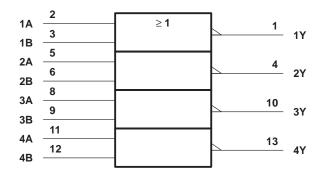
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logic symbol†

logic diagram, each gate (positive logic)





Pin numbers shown are for the D, DB, J, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V _{CC}	0.5 V to 7 V
Input voltage range, V _I (see Note 1)	\dots -0.5 V to V _{CC} + 0.5 V
Output voltage range, V _O (see Notes 1 and 2)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$)	±20 mA
Output clamp current, I _{OK} (V _O < 0 or V _O > V _{CC})	±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±25 mA
Continuous current through V _{CC} or GND	±50 mA
Maximum power dissipation at $T_A = 55^{\circ}C$ (in still air) (see Note 3): D package .	1.25 W
DB or PW pag	ckage 0.5 W
Storage temperature range, T _{stq}	–65°C to 150°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. This value is limited to 7 V maximum.
 - 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

recommended operating conditions (see Note 4)

			SN54	SN54LV02		54LV02 SN74LV02			UNIT	
			MIN	MAX	MIN	MAX	UNII			
Vсс	Supply voltage		2.7	5.5	2.7	5.5	V			
\/	High-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		2		V			
VIH	V _{CC} = 4.5 \		3.15	7	3.15		V			
VIL	Low lovel input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8		0.8	V			
	Low-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		1.65		1.65	V			
VI	Input voltage		0	Vcc	0	VCC	V			
۷o	Output voltage		9	VCC	0	VCC	V			
la	High-level output current	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	0	-6		-6				
IОН		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	Q	-12		-12	mA			
la.	Low level output ourrent	V _{CC} = 2.7 V to 3.6 V		6		6	mA			
IOL	Low-level output current $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$			12		12	IIIA			
Δt/Δν	Input transition rise or fall rate		0	100	0	100	ns/V			
T _A	Operating free-air temperature		-55	125	-40	85	°C			

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	v +	SN54LV02			SN74LV02			
	TEST CONDITIONS	v _{cc} †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
	I _{OH} = -100 μA	MIN to MAX	VCC - C).2		VCC - C).2		
Vон	$I_{OH} = -6 \text{ mA}$	3 V	2.4			2.4			V
	I _{OH} = -12 mA	4.5 V	3.6			3.6			
VoL	I _{OL} = 100 μA	MIN to MAX			0.2			0.2	
	I _{OL} = 6 mA	3 V		14	0.4			0.4	V
	I _{OL} = 12 mA	4.5 V		FL	0.55			0.55	
1.	V _I = V _{CC} or GND	3.6 V		,0	±1			±1	
ΙĮ		5.5 V	-	Ć)	±1			±1	μΑ
laa	$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V	Q		20			20	μΑ
lcc		5.5 V	S. C.		20			20	
ΔICC	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V			500			500	μΑ
C _i	V _I = V _{CC} or GND	3.3 V		2.5			2.5		nE
	Al - ACC or GIAD	5 V		2.5			2.5		pF

[†] For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER			SN54LV02					
	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 5 V \pm 0.5 V$	$V_{CC} = 3.3 V \pm 0.3 V$	$V_{CC} = 2.7 V$	UNIT		
			MIN TYP MAX	MIN TYP MAX	MIN MAX			
^t pd	А	Υ	5 10	8 13	16	ns		



SN54LV02, SN74LV02 QUADRUPLE 2-INPUT POSITIVE-NOR GATES

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switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER			SN74LV02								
	FROM (INPUT) (0	TO (OUTPUT)	V_{CC} = 5 V \pm 0.5 V		V_{CC} = 3.3 V \pm 0.3 V			$V_{CC} = 2.7 \text{ V}$		UNIT	
		(0011 01)	MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
^t pd	А	Υ		5	10		8	13		16	ns

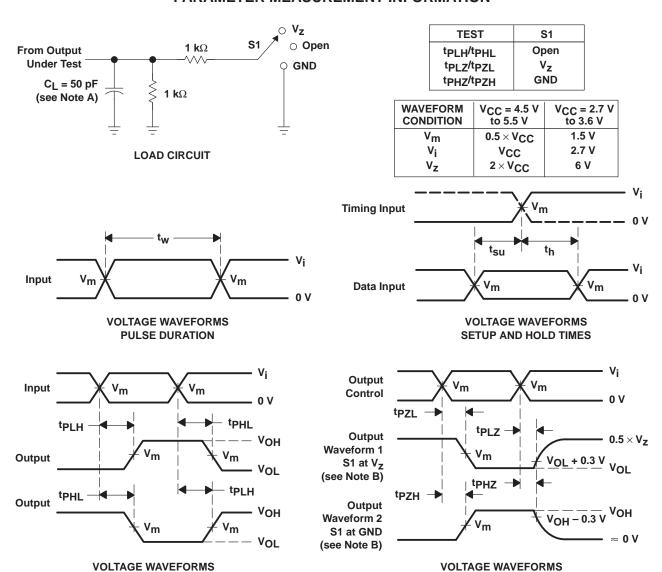
operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	VCC	TYP	UNIT
C _{pd} Power di	Power dissination conscitance per gets	C ₁ = 50 pF. f = 10 MHz	3.3 V	16	pF
	Power dissipation capacitance per gate	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	5 V	20	

ENABLE AND DISABLE TIMES

LOW- AND HIGH-LEVEL ENABLING

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.

PROPAGATION DELAY TIMES

INVERTING AND NONINVERTING OUTPUTS

- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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